



B120WS-F THRU B1100WS-F

1 Amperes Surface Mount Schottky Barrier Rectifiers
VOLTAGE : 20 TO 100Volts

| Features | Outline |
|--|---|
| <ul style="list-style-type: none"> • Low profile surface mounted application in order to optimize board space. • Low power loss, high efficiency. • High current capability, low forward voltage drop. • High surge capability. • Guardring for overvoltage protection. • Ultra high-speed switching. • Silicon epitaxial planar chip, metal silicon junction. • Suffix "G" indicates Halogen-free part, ex.B120WSG-F. • Lead-free parts meet environmental standards of MIL-STD-19500 /228 | <p>SOD-323F</p> <p>Dimensions in inches and (millimeters)</p> |
| Mechanical data | |
| <ul style="list-style-type: none"> • Epoxy:UL94-V0 rated flame retardant • Case : Molded plastic, SOD-323F • Terminals : Solder plated, solderable per MIL-STD-750, Method 2026 • Polarity : Indicated by cathode band • Weight : Approximated 0.008 gram | |

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

| Parameter | Symbol | B120WS-F | B130WS-F | B140WS-F | B160WS-F | B1100WS-F | UNIT |
|--|-----------|------------|----------|----------|----------|------------|------|
| Making code | | 12 | 13 | 14 | 16 | 10 | |
| Maximum Recurrent Peak Reverse Voltage | V_{RRM} | 20 | 30 | 40 | 60 | 100 | V |
| Maximum RMS Voltage | V_{RMS} | 14 | 21 | 28 | 42 | 70 | |
| Maximum DC Blocking Voltage | V_{DC} | 20 | 30 | 40 | 60 | 100 | |
| Maximum Instantaneous Forward Voltage@1.0A, $T_A = 25^\circ\text{C}$ | V_F | 0.50 | | | 0.70 | 0.81 | V |
| Operating Temperature | T_J | -50 ~ +125 | | | | -50 ~ +150 | °C |

| Parameter | Conditions | Symbol | MIN. | TYP. | MAX. | UNIT |
|----------------------------|--|-----------|------|------|------|------|
| Forward rectified current | See Fig. 1 | I_O | | | 1.0 | A |
| Forward surge current | 8.3ms single half sine-wave superimposed on rate load (JEDEC method) | I_{FSM} | | | 30 | A |
| Reverse current | $V_R = V_{RRM}$ $T_A = 25^\circ\text{C}$ | I_R | | | 0.1 | mA |
| | $V_R = V_{RRM}$ $T_A = 100^\circ\text{C}$ | | | | 20 | |
| Thermal resistance | Junction to ambient | R_{BJA} | | 88 | | °C/W |
| Diode junction capacitance | f=1MHz and applied 4V DC reverse voltage | C_J | | 120 | | pF |
| Storage temperature | | T_{STG} | -50 | | +150 | °C |



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Rating and characteristic curves

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

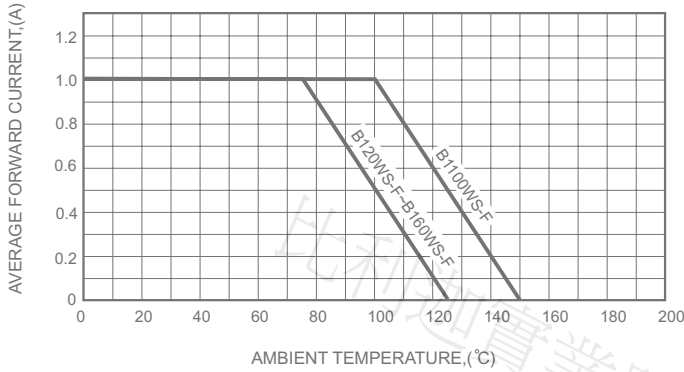


FIG.2-TYPICAL FORWARD CHARACTERISTICS

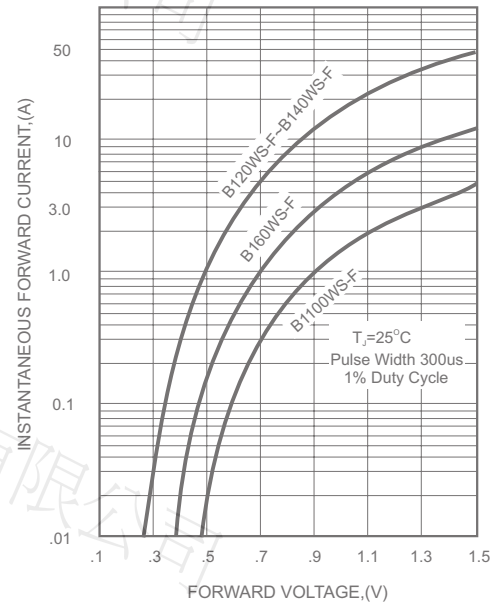


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

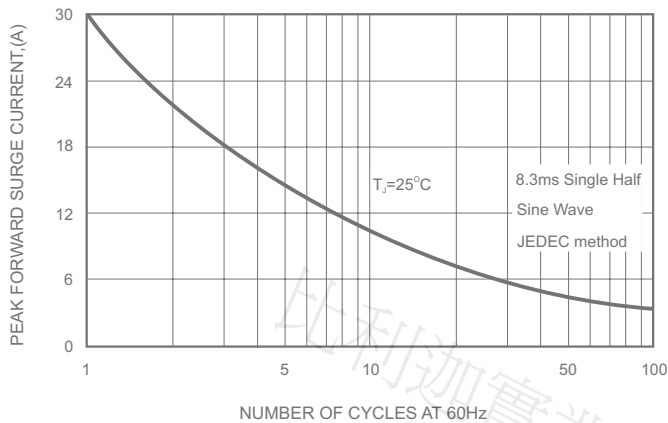


FIG.5 - TYPICAL REVERSE CHARACTERISTICS

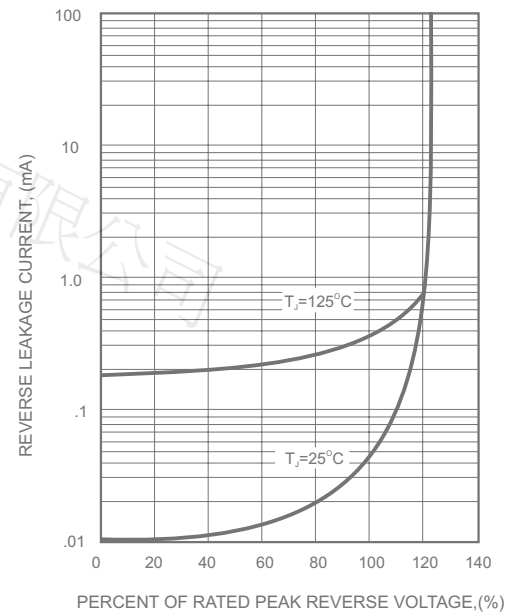


FIG.4-TYPICAL JUNCTION CAPACITANCE

